Frequency Multiplication with High-Power Microwave Field-Effect Transistors

M.S. Gupta, R.W. Laton and T.T. Lee. "Frequency Multiplication with High-Power Microwave Field-Effect Transistors." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 498-500.

The experimentally measured characteristics of a 4-to-8 GHz FET frequency doubler are described. A nonlinear circuit model for microwave FETs is proposed and is shown useful for predicting and optimizing the doubler performance, and for calculating the design parameters.

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